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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10010162	11/20/2001	438	400	2812	ROMAN, A

**APPLICANTS: Hshieh Fwu-luan; So Koon; Amato John; Pratt Brian;

**CONTINUING DATA VERIFIED: *None AR 06/30/03*

** FOREIGN APPLICATIONS VERIFIED: *None AR 06/30/03*

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>	
Foreign priority claimed 35 USC 119 conditions met		<input type="checkbox"/> yes <input checked="" type="checkbox"/> no <input type="checkbox"/> yes <input type="checkbox"/> no	ATTORNEY DOCKET NO
Verified and Acknowledged Examiners's initials		<i>AR 06/30/03</i>	GS 149

TITLE : Method of forming narrow trenches in semiconductor substrates

U.S.DEP'T OF COMM /PAT. & TM-PTO-436L(Rev. 12-94)

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Assistant Examiner	
		Total Claims	Print Claim for O.G
ISSUE FEE		DRAWING	
Amount Due	Date Paid	Sheets Drwg.	Figs.Drwg.
TERMINAL		Print Fig.	
DISCLAIMER		Primary Examiner	
		PREPARED FOR ISSUE	
		Applicant Examiner	
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